

PCN Number:	20220926000.2	PCN Date:	September 28, 2022
Title:	Qualification of new Fab site (RFAB) using qualified Process Technology, Die Revision, and additional BOM options for select devices		
Customer Contact:	PCN Manager	Dept:	Quality Services
Proposed 1st Ship Date:	Mar 28, 2023	Sample requests accepted until:	Oct 28, 2022*

***Sample requests received after Oct 28, 2022 will not be supported.**

Change Type:

<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process	<input checked="" type="checkbox"/>	Assembly Materials
<input checked="" type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>	Mechanical Specification
<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process
<input type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>	Wafer Bump Process
<input checked="" type="checkbox"/>	Wafer Fab Site	<input checked="" type="checkbox"/>	Wafer Fab Materials	<input checked="" type="checkbox"/>	Wafer Fab Process
		<input type="checkbox"/>	Part number change		

PCN Details

Description of Change:

Texas Instruments is pleased to announce the qualification of a new fab & process technology (RFAB, LBC9) and Assembly & BOM option for selected devices as listed below in the product affected section. Construction differences are noted below:

Current Fab Site			Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
SFAB	HCMOS	150 mm	RFAB	LBC9	300 mm

The die was also changed as a result of the process change.

Additionally, there will be a BOM options introduced for these devices:

What	Current	Additional
Mold Compound	4206193 or 4211471	4147858
Mount Compound	4042500 or 4147858	4147858

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
SH-BIP-1	SHE	USA	Sherman
RFAB	RFB	USA	Richardson

Die Rev:

Current	New
Die Rev [2P]	Die Rev [2P]
H, I	A

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS
 MADE IN: Malaysia
 2DC: 20:
 MSL '2 /260C/1 YEAR SEAL DT
 MSL 1 /235C/UNLIM 03/29/04
 OPT:
 ITEM: 39
 LBL: 5A (L)T0:1750

(1P) SN74LS07NSR
 (Q) 2000 (D) 0336
 (31T) LOT: 3959047MLA
 (4W) TKY (1T) 7523483SI2
 (P)
 (2P) REV: (V) 0033317
 (20L) CCO:CHE (21L) CCO:USA
 (22L) ASO:MLA (23L) ACO:MYS

Product Affected:

SN74LV08ATPWRG4Q1	SN74LV14ATPWRQ1	SN74LV32ATPWRG4Q1	SN74LV74AQPWRG4Q1
SN74LV11ATPWRG4Q1			

The following table provides the updated thermal characteristics to all devices contained within this PCN. All thermal values can be compared to the existing devices by reviewing the datasheets currently on TI.com. The impact to the customer system is anticipated to be negligible, however the customer must review their system design to assess any risk due to the change in thermal characteristics. Please see the table below which provides a summary of thermal values that some of the devices will be updated to based on each pin/pkg combination. The below table only applies to the following devices: SN74LV14ATPWRQ1. The datasheets/thermal values for the other devices in this PCN will not be changed as a result of the changes in this PCN.

THERMAL METRIC		PW	UNIT
		(TSSOP)	
		14	
		PINS	
RθJA	Junction-to-ambient thermal resistance	151.0	°C/W
RθJC(top)	Junction-to-case (top) thermal resistance	80.0	°C/W
RθJB	Junction-to-board thermal resistance	94.2	°C/W
ψJT	Junction-to-top characterization parameter	28.0	°C/W
ψJB	Junction-to-board characterization parameter	93.6	°C/W
RθJC(bot)	Junction-to-case (bottom) thermal resistance	N/A	°C/W

TI Information
Selective Disclosure

Automotive New Product Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)

BD5_LVA_14PW_MLA_Q1
Approve Date 20-September-2022

Product Attributes

Attributes	Qual Device: SN74LV08ATPWG4Q1	Qual Device: SN74LV11ATPWG4Q1	Qual Device: SN74LV14ATPWQ1	Qual Device: SN74LV32ATPWG4Q1	Qual Device: SN74LV74AQPWG4Q1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: ADS131B84QPWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Logic	Logic	Logic	Logic	Logic	-	Signal Chain
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB
Assembly Site	MLA	MLA	MLA	MLA	MLA	MLA	MLA
Package Group	TSSOP	TSSOP	TSSOP	TSSOP	TSSOP	TSSOP	TSSOP
Package Designator	PW	PW	PW	PW	PW	PW	PW
Pin Count	14	14	14	14	14	14	20

- QBS: Qual By Similarity
- Qual Device SN74LV08ATPWG4Q1 is qualified at MSL1 260C
- Qual Device SN74LV11ATPWG4Q1 is qualified at MSL1 260C
- Qual Device SN74LV14ATPWQ1 is qualified at MSL1 260C
- Qual Device SN74LV32ATPWG4Q1 is qualified at MSL1 260C
- Qual Device SN74LV74AQPWG4Q1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: SN74LV08ATPWG4Q1	Qual Device: SN74LV11ATPWG4Q1	Qual Device: SN74LV14ATPWQ1	Qual Device: SN74LV32ATPWG4Q1	Qual Device: SN74LV74AQPWG4Q1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: ADS131B84QPWRQ1
Test Group A - Accelerated Environment Stress Tests														
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	1 Step	-	-	-	-	-	3/0/0	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	1 Step	-	-	-	-	-	-	3/0/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	-	-	-	3/231/0	3/231/0

ACU/HAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	-	-	-	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	-	-	3/231/0	3/231/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	-	-	3/135/0	1/45/0
Test Group B - Accelerated Lifetime Simulation Tests														
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	-	-	-	-	-	3/231/0	-
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	150C	300 Hours	-	-	1/77/0	-	-	-	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	-	-	-	-	-	3/2400/0	-
Test Group C - Package Assembly Integrity Tests														
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpl>1.67	Wires	-	-	-	-	-	3/9/0	3/9/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpl>1.67	Wires	-	-	-	-	-	3/9/0	3/9/0
SD	C3	JEDEC JESD22-B102	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	-	-	1/15/0	-
SD	C3	JEDEC JESD22-B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	-	-	1/15/0	-
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpl>1.67	-	-	-	-	-	-	3/3/0	-
Test Group D - Die Fabrication Reliability Tests														
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDD	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests														
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	4000 Volts	-	-	1/3/0	-	1/3/0	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	1500 Volts	-	-	1/3/0	-	1/3/0	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	-	-	1/6/0	-	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpl>1.67 Room, hot, and cold	-	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	3/9/0	3/9/0
Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device	Qual Device	Qual Device	Qual Device	Qual Device	QBS Reference	QBS Reference

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E) : -40C to +125C
- Grade 1 (or Q) : -40C to +125C
- Grade 2 (or T) : -40C to +125C
- Grade 3 (or R) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : ACU/HAST

Quality and Environmental data is available at TIs external Web site: <http://www.ti.com/>

TI Qualification ID: R-NPD-2111-088

Automotive New Product Qualification Summary
(As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

BD5_LVA_14PW_MLA_Q1
Approve Date 20-September-2022

Product Attributes

Attributes	Qual Device: SN74LV08ATPWRG4Q1	Qual Device: SN74LV11ATPWRG4Q1	Qual Device: SN74LV14ATPWRQ1	Qual Device: SN74LV32ATPWRG4Q1	Qual Device: SN74LV74AQPWRG4Q1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: ADS131B04QPWRQ1
Die Attributes							
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB	RFAB
Package Attributes							
Assembly Site	MLA	MLA	MLA	MLA	MLA	MLA	MLA
Package Group	TSSOP	TSSOP	TSSOP	TSSOP	TSSOP	TSSOP	TSSOP
Package Designator	PW	PW	PW	PW	PW	PW	PW
Pin Count	14	14	14	14	14	14	20

- QBS: Qual By Similarity
- Qual Device SN74LV08ATPWRG4Q1 is qualified at MSL1 260C
- Qual Device SN74LV11ATPWRG4Q1 is qualified at MSL1 260C
- Qual Device SN74LV14ATPWRQ1 is qualified at MSL1 260C
- Qual Device SN74LV32ATPWRG4Q1 is qualified at MSL1 260C
- Qual Device SN74LV74AQPWRG4Q1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: SN74LV08ATPWRG4Q1	Qual Device: SN74LV11ATPWRG4Q1	Qual Device: SN74LV14ATPWRQ1	Qual Device: SN74LV32ATPWRG4Q1	Qual Device: SN74LV74AQPWRG4Q1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: ADS131B04QPWRQ1
Test Group A - Accelerated Environment Stress Tests														
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	1 Step	-	-	-	-	-	3/0/0	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	1 Step	-	-	-	-	-	-	1/0/0
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	-	-	-	-	-	3/66/0	1/22/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	-	-	-	-	-	3/66/0	1/22/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	-	-	-	3/231/0	1/77/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	-	-	-	-	3/3/0	1/0/0
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-	-	-	-	-	3/9/0	1/0/0
HAST	A2.1.4	-	3	30	Bond Pull over Sitch, post bHAST, 1X	Post stress	Wires	-	-	-	-	-	3/9/0	1/0/0
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	-	-	-	-	-	3/9/0	1/0/0
HAST	A2.2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	192 Hours	-	-	-	-	-	3/231/0	1/70/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST, 2X	Review for delamination	Completed	-	-	-	-	-	3/66/0	1/22/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	-	-	-	-	-	3/3/0	1/1/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	-	-	-	-	-	3/9/0	1/3/0
HAST	A2.2.4	-	3	30	Bond Pull over Sitch, post bHAST, 2X	Post stress	Wires	-	-	-	-	-	3/9/0	1/3/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	-	-	-	-	-	3/9/0	1/3/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	-	-	3/231/0	1/77/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC, 1X	Review for delamination	Completed	-	-	-	-	-	3/66/0	1/22/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-	-	-	-	3/3/0	1/0/0
TC	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-	-	-	-	-	3/9/0	1/3/0
TC	A4.1.4	-	3	30	Bond Pull over Sitch, post TC, 1X	Post stress	Wires	-	-	-	-	-	3/9/0	1/3/0
TC	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	-	-	-	-	-	3/9/0	1/3/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	-	-	-	-	-	3/231/0	1/70/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	-	-	-	-	-	3/66/0	1/22/0

TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	-	-	-	-	-	3/30	1/10
TC	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	-	-	-	-	-	3/30	1/30
TC	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	-	-	-	-	-	3/30	1/30
TC	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	-	-	-	-	-	3/30	1/30
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	-	-	3/1350	144/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	-	-	-	-	3/30	1/10
HTSL	A6.2	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	2000 Hours	-	-	-	-	-	3/1350	144/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	-	-	-	-	-	3/30	1/10
Test Group B - Accelerated Lifetime Simulation Tests														
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	-	-	-	-	-	3/231/0	-
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	150C	300 Hours	-	-	1/770	-	-	-	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	-	-	-	-	-	3/2400/0	-
Test Group C - Package Assembly Integrity Tests														
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	-	-	-	3/90/0	3/90/0
WBP	C2	ML-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	-	-	-	3/90/0	3/90/0
SD	C3	JEDEC JESD22-B102	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	-	-	1/15/0	-
SD	C3	JEDEC JESD22-B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	-	-	1/15/0	-
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	-	-	-	-	3/30/0	-
Test Group D - Die Fabrication Reliability Tests														
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDD	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

EI (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold: HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room: ACU/HAST

Quality and Environmental data is available at TIs external Web site: <http://www.ti.com>

TI Qualification ID: R-NPD-2111-088

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
WW Change Management Team	PCN_ww_admin_team@list.ti.com

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